

**Date Mailed: April 18, 2006**

Sheet 1 of 1

<b>FORM 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b>  <b>IN AN APPLICATION</b> (Use several sheets if necessary)	Docket Number: 10873.1420US01	Application Number: 10/804,610
	Applicant: KITAOKA, et al.	
	Filing Date: March 18, 2004	Group Art Unit: 2818

<b>U.S. PATENT DOCUMENTS</b>								
<b>EXAMINER INITIAL</b>	<b>DOCUMENT NO.</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUBCLASS</b>	<b>FILING DATE IF APPROPRIATE</b>		
TH ↓  	6,121,121	September, 2000	Koide	438	481	—		
	6,503,610	January, 2003	Hiramatsu, et al.	428	210	—		
	6,667,252	December, 2003	Miyajima, et al.	438	796	—		
	2005/0082564	April, 2005	Kitaoka, et al.	257	103	—		
<b>FOREIGN PATENT DOCUMENTS</b>								
	<b>DOCUMENT NO.</b>	<b>DATE</b>	<b>COUNTRY</b>	<b>CLASS</b>	<b>SUBCLASS</b>	<b>TRANSLATION</b>		
						<b>YES</b>	<b>NO</b>	
TH	3409576	March, 2003	Japan			Abstract		
TH	2000-357663	December, 20003	Japan			Abstract		
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>								
TH		Kawamura, et al., "Growth of a Large GaN Single Crystal Using the Liquid Phase Epitaxy (LPE) Technique", Jpn. J. Appl. Phys., vol. 42, part 2, no. 1A/B, January 15, 2003, pp. L4-L6						

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**PATENT TRADEMARK OFFICE**

EXAMINER	/Tu Tu Ho/ (06/16/2006)	DATE CONSIDERED	06/16/2006
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.			

\*Substitute Disclosure Statement Form (PTO-1449)

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